

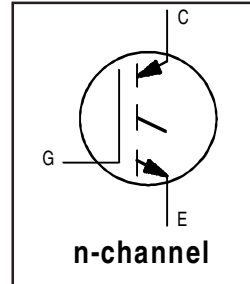
IRG4PH50S

INSULATED GATE BIPOLAR TRANSISTOR

Standard Speed IGBT

Features

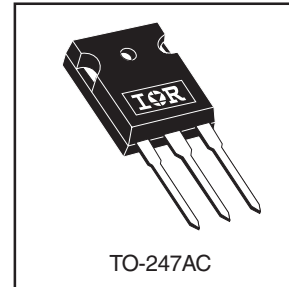
- Standard: Optimized for minimum saturation voltage and low operating frequencies (< 1kHz)
- Generation 4 IGBT design provides tighter parameter distribution and higher efficiency than Generation 3
- Industry standard TO-247AC package



$V_{CES} = 1200V$
$V_{CE(on) typ.} = 1.47V$
@ $V_{GE} = 15V, I_C = 33A$

Benefits

- Generation 4 IGBT's offer highest efficiency available
- IGBT's optimized for specified application conditions
- Designed to be a "drop-in" replacement for equivalent industry-standard Generation 3 IR IGBT's



Absolute Maximum Ratings

	Parameter	Max.	Units
V_{CES}	Collector-to-Emitter Voltage	1200	V
$I_C @ T_C = 25^\circ C$	Continuous Collector Current	57	A
$I_C @ T_C = 100^\circ C$	Continuous Collector Current	33	
I_{CM}	Pulsed Collector Current ^①	114	
I_{LM}	Clamped Inductive Load Current ^②	114	
V_{GE}	Gate-to-Emitter Voltage	± 20	V
E_{ARV}	Reverse Voltage Avalanche Energy ^③	270	mJ
$P_D @ T_C = 25^\circ C$	Maximum Power Dissipation	200	W
$P_D @ T_C = 100^\circ C$	Maximum Power Dissipation	80	
T_J	Operating Junction and Storage Temperature Range	-55 to +150	°C
T_{STG}			
	Mounting torque, 6-32 or M3 screw.	10 lbf•in (1.1N•m)	

Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	0.64	°C/W
$R_{\theta CS}$	Case-to-Sink, Flat, Greased Surface	0.24	—	
$R_{\theta JA}$	Junction-to-Ambient, typical socket mount	—	40	
Wt	Weight	6.0 (0.21)	—	g (oz)

Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)CES}$	Collector-to-Emitter Breakdown Voltage	1200	—	—	V	$V_{GE} = 0V, I_C = 250\mu A$
$V_{(BR)ECS}$	Emitter-to-Collector Breakdown Voltage ④	18	—	—	V	$V_{GE} = 0V, I_C = 1.0 A$
$\Delta V_{(BR)CES}/\Delta T_J$	Temperature Coeff. of Breakdown Voltage	—	1.22	—	V/°C	$V_{GE} = 0V, I_C = 2.0 mA$
$V_{CE(ON)}$	Collector-to-Emitter Saturation Voltage	—	1.47	1.7	V	$I_C = 33A, V_{GE} = 15V$ See Fig.2, 5
		—	1.75	—		
		—	1.55	—		
$V_{GE(th)}$	Gate Threshold Voltage	3.0	—	6.0		$V_{CE} = V_{GE}, I_C = 250\mu A$
$DV_{GE(th)}/DT_J$	Temperature Coeff. of Threshold Voltage	—	-11	—	mV/°C	$V_{CE} = V_{GE}, I_C = 250\mu A$
g_{fe}	Forward Transconductance ⑤	27	40	—	S	$V_{CE} = 100V, I_C = 33A$
I_{CES}	Zero Gate Voltage Collector Current	—	—	250	μA	$V_{GE} = 0V, V_{CE} = 1200V$
		—	—	2.0		$V_{GE} = 0V, V_{CE} = 10V, T_J = 25^\circ\text{C}$
		—	—	1000		$V_{GE} = 0V, V_{CE} = 1200V, T_J = 150^\circ\text{C}$
I_{GES}	Gate-to-Emitter Leakage Current	—	—	± 100	nA	$V_{GE} = \pm 20V$

Switching Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
Q_g	Total Gate Charge (turn-on)	—	167	251	nC	$I_C = 33A$ $V_{CC} = 400V$ See Fig. 8 $V_{GE} = 15V$
Q_{ge}	Gate - Emitter Charge (turn-on)	—	25	38		
Q_{gc}	Gate - Collector Charge (turn-on)	—	55	83		
$t_{d(on)}$	Turn-On Delay Time	—	32	—	ns	$T_J = 25^\circ\text{C}$ $I_C = 33A, V_{CC} = 960V$ $V_{GE} = 15V, R_G = 5.0\Omega$ Energy losses include "tail"
t_r	Rise Time	—	29	—		
$t_{d(off)}$	Turn-Off Delay Time	—	845	1268		
t_f	Fall Time	—	425	638		
E_{on}	Turn-On Switching Loss	—	1.80	—	mJ	See Fig. 9, 10, 14
E_{off}	Turn-Off Switching Loss	—	19.6	—		
E_{ts}	Total Switching Loss	—	21.4	44		
$t_{d(on)}$	Turn-On Delay Time	—	32	—	ns	$T_J = 150^\circ\text{C},$ $I_C = 33A, V_{CC} = 960V$ $V_{GE} = 15V, R_G = 5.0\Omega$ Energy losses include "tail"
t_r	Rise Time	—	30	—		
$t_{d(off)}$	Turn-Off Delay Time	—	1170	—		
t_f	Fall Time	—	1000	—		
E_{ts}	Total Switching Loss	—	37	—	mJ	See Fig. 10,11,14
L_E	Internal Emitter Inductance	—	13	—	nH	Measured 5mm from package
C_{ies}	Input Capacitance	—	3600	—	pF	$V_{GE} = 0V$ $V_{CC} = 30V$ See Fig. 7 $f = 1.0MHz$
C_{oes}	Output Capacitance	—	160	—		
C_{res}	Reverse Transfer Capacitance	—	30	—		

Notes:

- ① Repetitive rating; $V_{GE} = 20V$, pulse width limited by max. junction temperature. (See fig. 13b)
- ② $V_{CC} = 80\%(V_{CES}), V_{GE} = 20V, L = 10\mu H, R_G = 5.0\Omega,$ (See fig. 13a)
- ③ Repetitive rating; pulse width limited by maximum junction temperature.
- ④ Pulse width $\leq 80\mu s$; duty factor $\leq 0.1\%$.
- ⑤ Pulse width $5.0\mu s$, single shot.

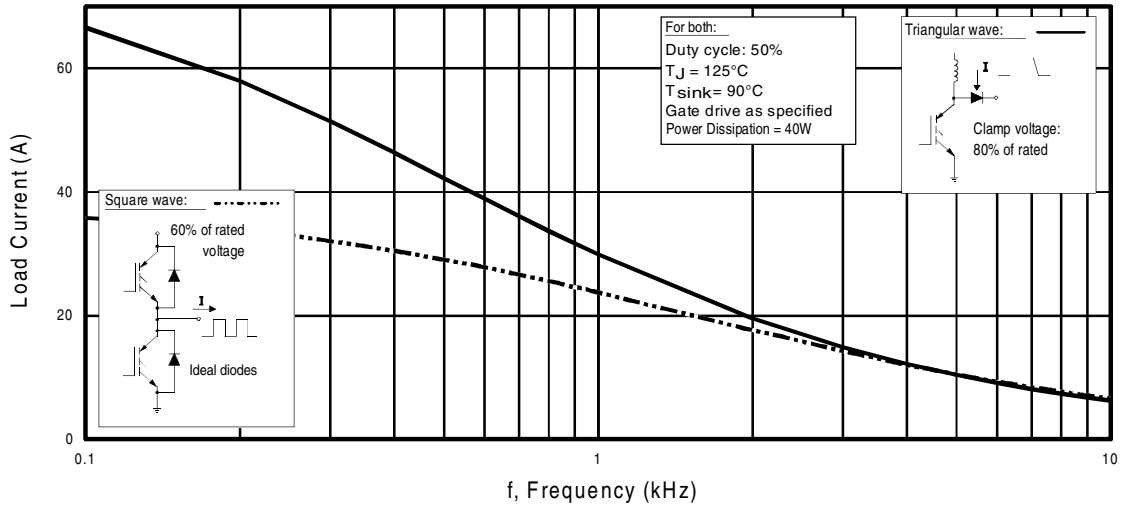


Fig. 1 - Typical Load Current vs. Frequency
(Load Current = I_{RMS} of fundamental)

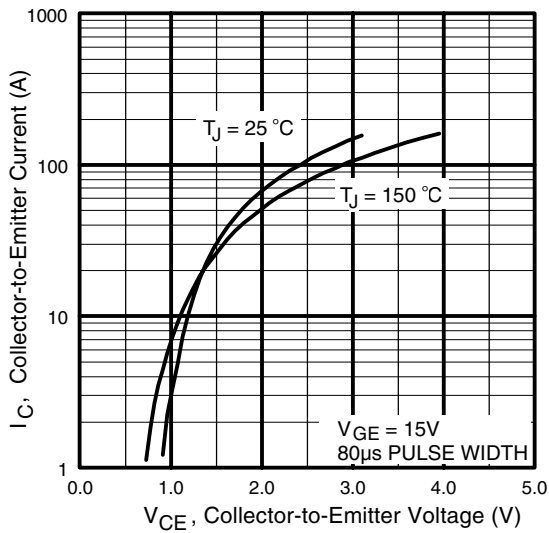


Fig. 2 - Typical Output Characteristics

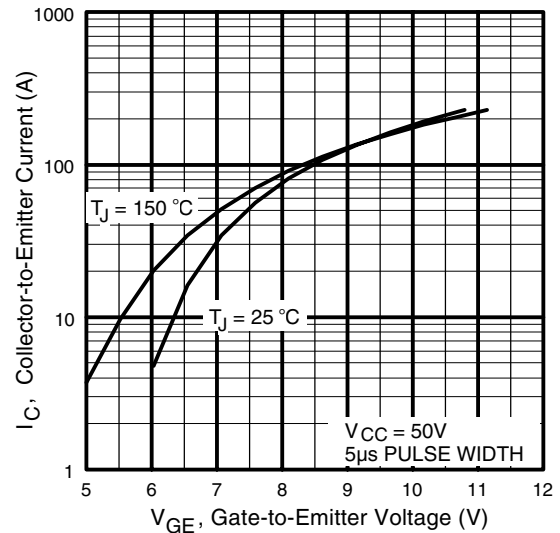


Fig. 3 - Typical Transfer Characteristics

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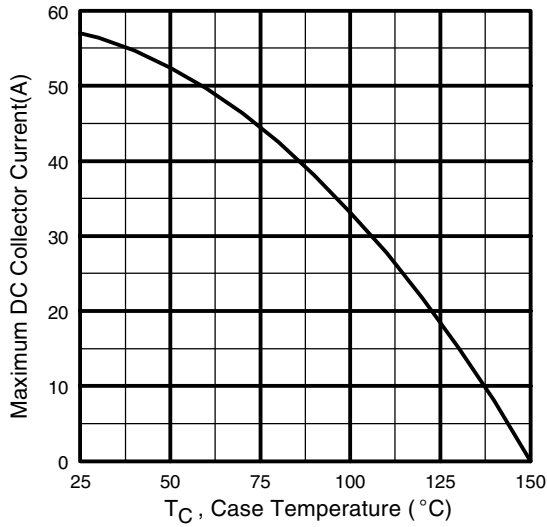


Fig. 4 - Maximum Collector Current vs. Case Temperature

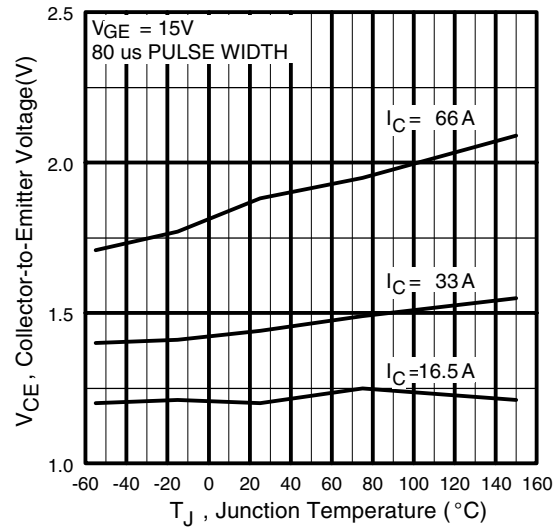


Fig. 5 - Typical Collector-to-Emitter Voltage vs. Junction Temperature

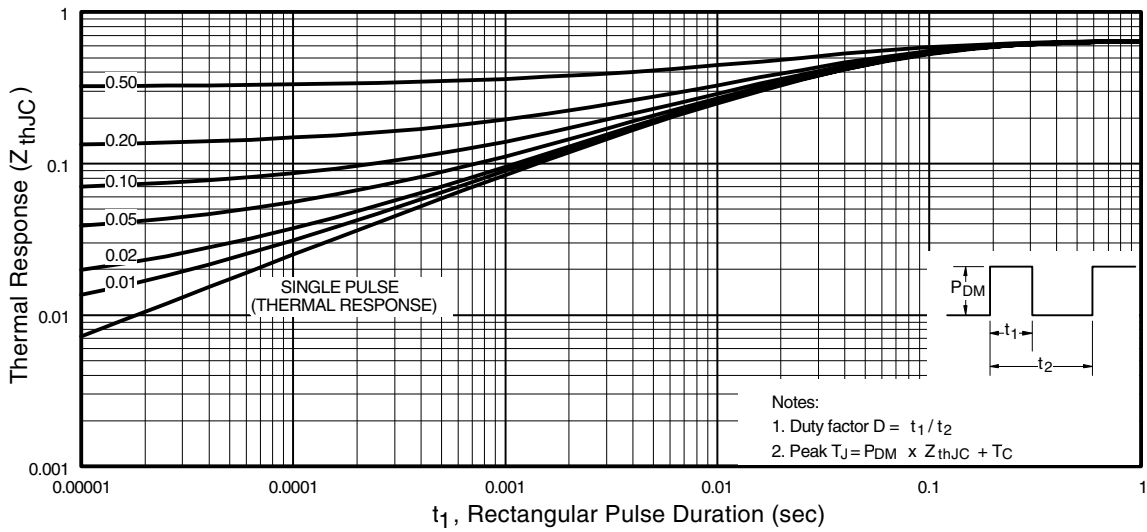


Fig. 6 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

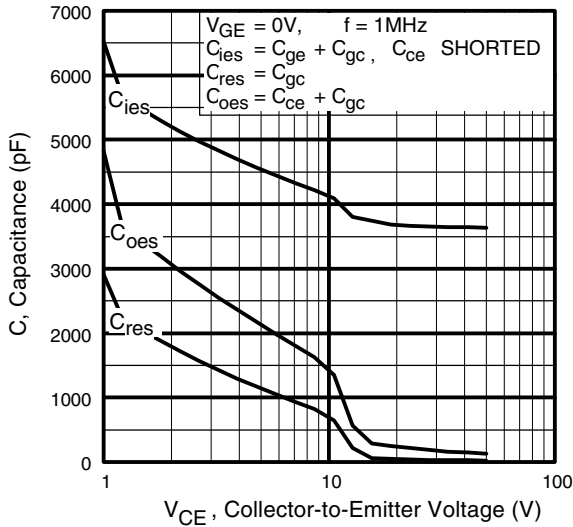


Fig. 7 - Typical Capacitance vs. Collector-to-Emitter Voltage

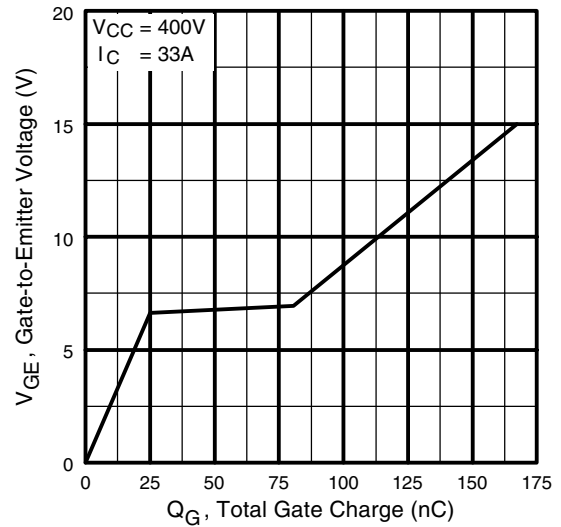


Fig. 8 - Typical Gate Charge vs. Gate-to-Emitter Voltage

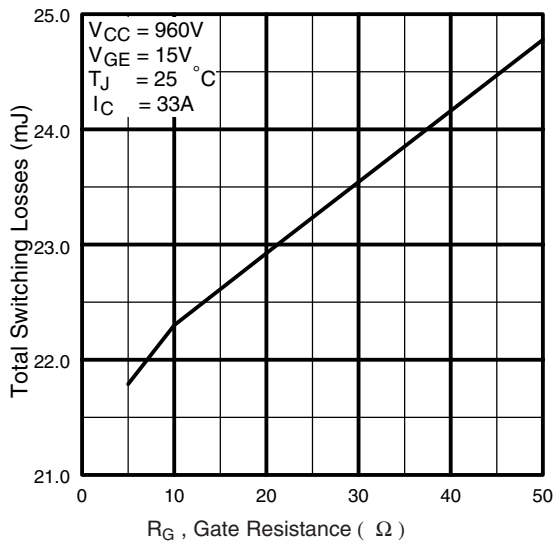


Fig. 9 - Typical Switching Losses vs. Gate Resistance

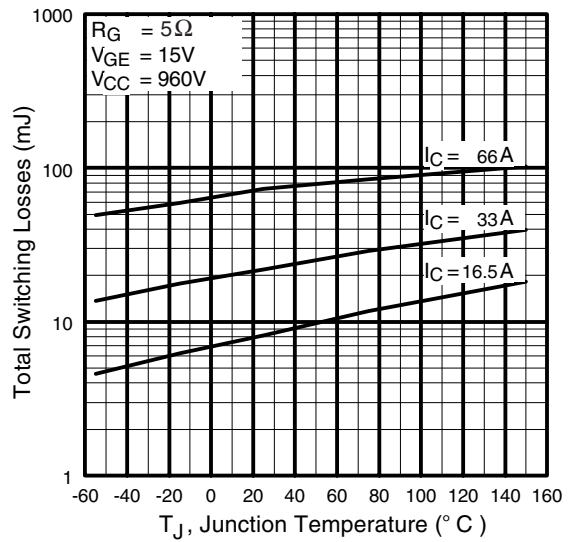


Fig. 10 - Typical Switching Losses vs. Junction Temperature

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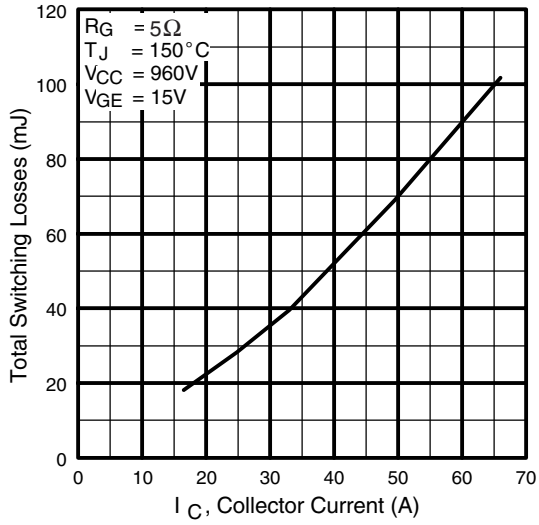


Fig. 11 - Typical Switching Losses vs. Collector-to-Emitter Current

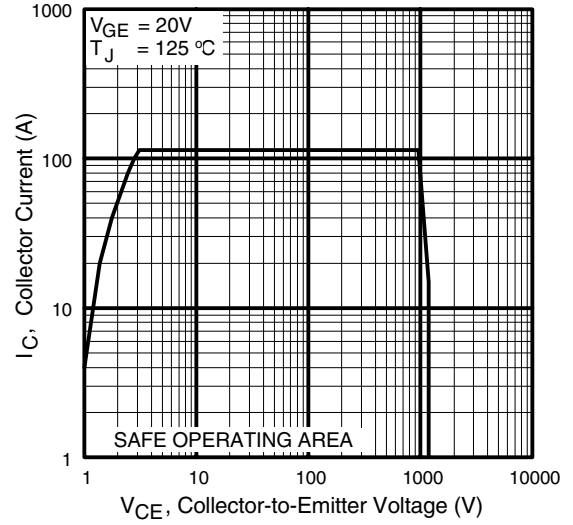


Fig. 12 - Reverse Bias SOA

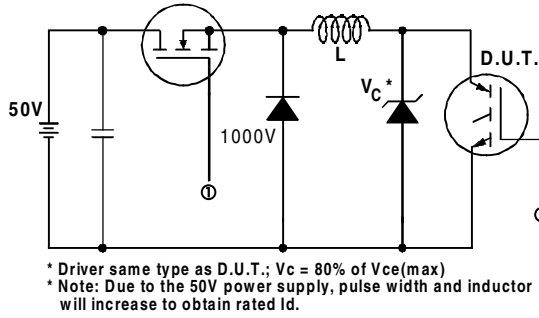


Fig. 13a - Clamped Inductive Load Test Circuit

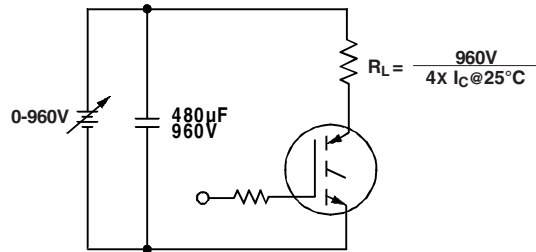


Fig. 13b - Pulsed Collector Current Test Circuit

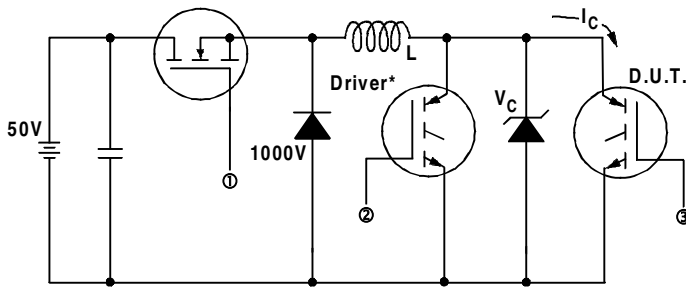


Fig. 14a - Switching Loss Test Circuit

* Driver same type as D.U.T., VC = ---V

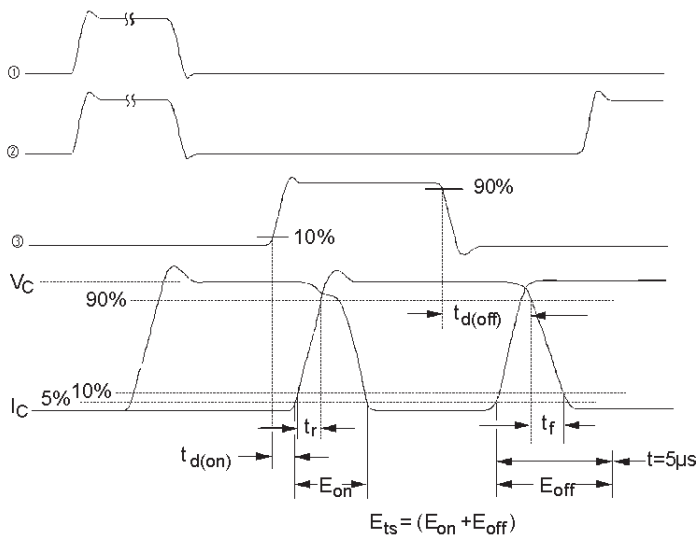
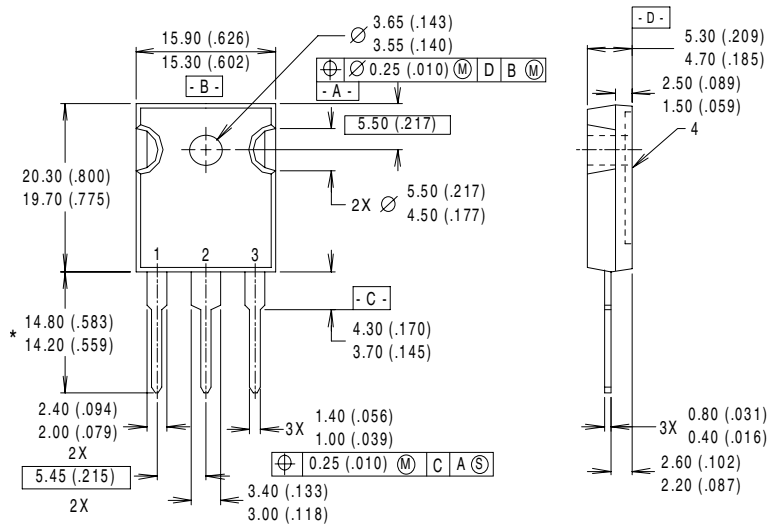


Fig. 14b - Switching Loss Waveforms

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Case Outline and Dimensions — TO-247AC



NOTES:

- 1 DIMENSIONS & TOLERANCING PER ANSI Y14.5M, 1982.
- 2 CONTROLLING DIMENSION : INCH.
- 3 DIMENSIONS ARE SHOWN MILLIMETERS (INCHES).
- 4 CONFORMS TO JEDEC OUTLINE TO-247AC.

LEAD ASSIGNMENTS

- 1 - GATE
- 2 - COLLECTOR
- 3 - EMITTER
- 4 - COLLECTOR

* LONGER LEADED (20mm) VERSION AVAILABLE (TO-247AD) TO ORDER ADD "E" SUFFIX TO PART NUMBER

CONFORMS TO JEDEC OUTLINE TO-247AC (TO-3P)

Dimensions in Millimeters and (Inches)

International
IR Rectifier

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Data and specifications subject to change without notice. 7/00